

Picraux Leads MRS in 1993

Tom Picraux is the 1993 President of the Materials Research Society, a position he assumes automatically from his elected office of First Vice President in 1992. While Picraux sees himself as only one player in a large cast of contributors to MRS, he looks forward to guiding the society as it celebrates its 20th anniversary. "I can think of no other professional society that could be as exciting to lead," he says.

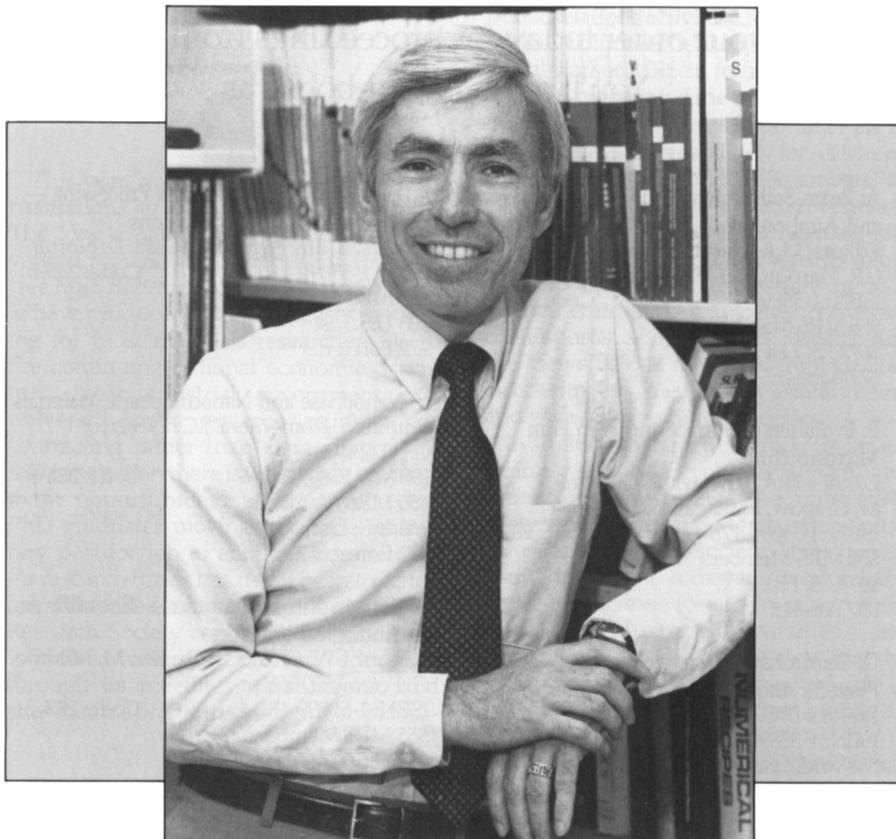
Picraux would like to see MRS contribute more broadly to the materials community. He plans to accomplish this by expanding technical representation within MRS, by enhancing MRS contributions to national and international science policy, and by promoting the recognition of materials research as a significant and fundamental branch of science.

Picraux believes MRS can maintain its quality and vitality, while continuing to grow as a society, simply by building on the successful formula it currently employs. "We have to keep our technically strong people highly involved," he says. "It is through the strength and creativity of dedicated volunteers and the flexibility of our technical program that we are able to produce meetings that reflect the materials trends of the times and the interests of our members."

"Another factor contributing to the vitality of MRS," says Picraux, "is the way in which our volunteers interact with our staff." It is important, he says, that MRS volunteers determine the technical content and the direction of the society, while the professional staff provides the high-level organization required for putting the society's plans into action in a timely and professional way. This balance makes it possible for MRS to respond quickly to significant materials developments, while keeping society activities driven by the active members.

Picraux first became active in MRS in the late 1970s, during the early days of laser annealing. He chaired several symposia in the 1980s, but the challenge of chairing the 1987 Fall Meeting won his allegiance to MRS. Afterward, he served as Program Committee Chair and was a Councillor of the Society from 1988 until 1990. In 1991 he was elected Second Vice President, and the following year, First Vice President.

A native of Missouri, Tom Picraux grew up on a farm, amidst strawberries, hay, and wheat. After high school he attended the University of Missouri, where he re-



ceived a BS degree in electrical engineering. Picraux then went on to Cambridge University as a Fulbright Fellow in physics, and later received his PhD degree in engineering science and physics from the California Institute of Technology.

Picraux is manager of the Semiconductor Physics Research Department at Sandia National Laboratories. He joined Sandia in 1969 as a member of the technical staff in ion-solid interactions research. Since 1972 he has managed various solid-state science activities at Sandia, including ion beam science, surface and interface science, defect physics, microsensor research, and semiconductor physics. Picraux is recognized for his development of ion channeling and its application to materials research. In 1990 he received the Department of Energy's E.O. Lawrence Award for materials research, based on this work.

Picraux has published more than 200 papers, and has served on such National Research Council studies as the 1986 *Materials Science Briefing on Advanced Processing of*

Electronic Materials in the United States and Japan, and the 1988 *Study on Photonics*. He was a founding editor and, until 1992, co-editor of the *Journal of Nuclear Instruments and Methods, Section B*, and currently serves on the editorial boards of several journals.

During the 1970s and 1980s, Picraux served on international conference committees on ion beam analysis and materials modification. He is a fellow of APS and was chair of the APS Materials Physics Division during 1990–91. He has also served on advisory boards at Argonne, Lawrence Livermore, and Lawrence Berkeley National Laboratories, and at the University of Texas at Austin.

Picraux enjoys traveling, and has been a visiting scientist at Aarhus University, Catania University, AT&T Bell Labs, Chalk River Labs, and Hughes Research Labs. This year he anticipates that his travels will take him to Strasbourg for the E-MRS meeting and to Tokyo for ICAM-93, the IUMRS-sponsored meeting on advanced materials. □

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